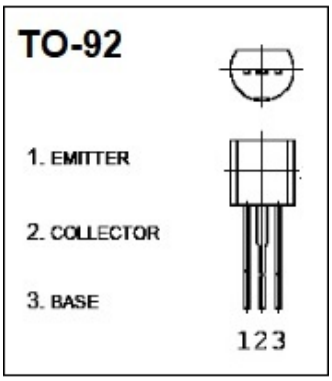
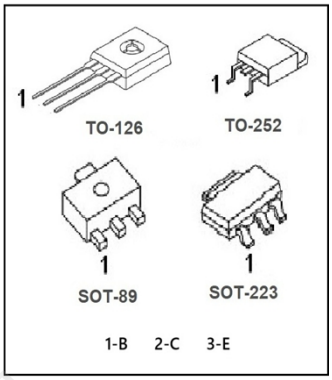
鼎德丰
DING DE FENG

PNP Silicon Transistor

B772

- **Complementary to D882**
- **Package:TO-126/TO-252/SOP-89/SOT-223/TO-92**





Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating		Unit
Collector-base voltage	BV_{CBO}	-40		V
Collector-emitter voltage	BV_{CEO}	-30		V
Emitter-base voltage	BV_{EBO}	-6		V
Collector current	I_{CM}	3		A
Collector Power Dissipation	P_C	TO-126	1	W
		TO-252	1.25	
		SOP-89	0.5	
		SOT-223	1	
		TO-92	0.625	
Junction Temperature	Tj	150		℃
Storage Temperature	Tstg	-55～+150		℃

Electrical Characteristics（Ta=25℃）

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=-100μA，I_E=0	-40		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=-1mA，I_B=0	-30		V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=-100μA，I_C=0	-6		V
collector-base cut-off current	I_{CBO}	V_{CB}=-40V，I_E=0		-1	μA
collector-emitter cut-off current	I_{CEO}	V_{CE}=-30V，I_B=0		-10	μA
emitter-base cut-off current	I_{EBO}	V_{EB}=-6V，I_C=0		-1	μA
DC current gain	H_{FE1}	V_{CE}=-2V，I_C=-1A	60	400	
	H_{FE2}	V_{CE}=-1V，I_C=-100mA	30		
collector-emitter saturation voltage	V_{CESAT}	I_C=-2A，I_B=-200mA		-0.5	V
Base-Emitter Saturation Voltage	V_{BESAT}	I_C=-2A，I_B=-200mA		-1.2	
Transition frequency	f_T	V_{CE}=-5V，I_C=-100 mA	50		MHz

Classification of H_{FE}

Rank	R	Q	P	E
Range	60-120	100-200	160-320	200-400

DDF
DDF
DDF